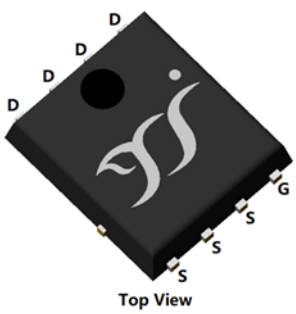
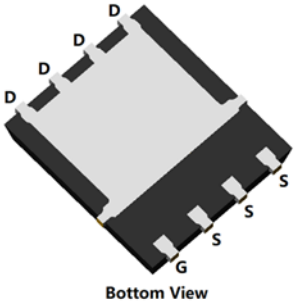
N-Channel Enhancement Mode Field Effect Transistor

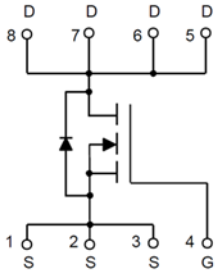


Top View



Bottom View

PDFN5060-8L



Product Summary

- V_{DS} 30V
- I_D 50A
- $R_{DS(ON)}$(at V_{GS}= 10V) ＜6.0mohm
- $R_{DS(ON)}$(at V_{GS}= 4.5V) ＜8.0mohm
- 100% EAS Tested
- 100% ▽V_{DS} Tested

General Description

- Trench Power LV MOSFET technology
- Excellent package for heat dissipation
- High density cell design for low $R_{DS(ON)}$
- Moisture Sensitivity Level 1
- Epoxy Meets UL 94 V-0 Flammability Rating
- Halogen Free

Applications

- High current load applications
- Load switch
- Hard switched and high frequency circuits
- Uninterruptible power supply

■ Absolute Maximum Ratings (T_A=25℃unless otherwise noted)

Parameter		Symbol	Limit	Unit
Drain-source Voltage		V_{DS}	30	V
Gate-source Voltage		V_{GS}	±20	V
Drain Current	T_C=25℃	I_D	50	A
	T_C=100℃		32	
Pulsed Drain Current [A]		I_{DM}	190	A
Total Power Dissipation [B]	T_C=25℃	P_D	45	W
	T_C=100℃		18	W
Total Power Dissipation @ T_A=25℃ [C]		P_D	6.0	W
Single Pulse Avalanche Energy [D]		E_{AS}	98	mJ
Thermal Resistance Junction-to-Case		$R_{\theta JC}$	2.8	℃/ W
Thermal Resistance Junction-to-Ambient		$R_{\theta JA}$	21	℃/ W
Junction and Storage Temperature Range		T_J ,T_{STG}	-55～+150	℃

■ Ordering Information (Example)

PREFERED P/N	PACKING CODE	Marking	MINIMUM PACKAGE(pcs)	INNER BOX QUANTITY(pcs)	OUTER CARTON QUANTITY(pcs)	DELIVERY MODE
YJG50N03B	F1	YJG50N03B	5000	10000	100000	13“ reel

■ Electrical Characteristics (T_J=25℃ unless otherwise noted)

Parameter	Symbol	Conditions	Min	Typ	Max	Units
Static Parameter						
Drain-Source Breakdown Voltage	BV_{DSS}	V_{GS}= 0V, I_D=250μA	30			V
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS}=30V,V_{GS}=0V			1	μA
Gate-Body Leakage Current	I_{GSS}	V_{GS}= ±20V, V_{DS}=0V			±100	nA
Gate Threshold Voltage	$V_{GS(th)}$	V_{DS}= V_{GS}, I_D=250μA	1	1.5	2.5	V
Static Drain-Source On-Resistance	$R_{DS(ON)}$	V_{GS}=10V, I_D=20A		3.9	6.0	mΩ
		V_{GS}= 4.5V, I_D=15A		6.0	8.0	
Diode Forward Voltage	V_{SD}	I_S=20A,V_{GS}=0V		0.85	1.2	V
Maximum Body-Diode Continuous Current	I_S				80	A
Gate Resistance	Rg	f =1 MHz		2.3		Ω
Dynamic Parameters						
Input Capacitance	C_{iss}	V_{DS}=15V,V_{GS}=0V,f=1MHZ		2191		pF
Output Capacitance	C_{oss}			300		
Reverse Transfer Capacitance	C_{rss}			247		
Switching Parameters						
Total Gate Charge	Q_g	V_{GS}=10V,V_{DS}=15V,I_D=20A		46.3		nC
Gate-Source Charge	Q_{gs}			8.8		
Gate-Drain Charge	Q_{gd}			9.2		
Reverse Recovery Chrage	Q_{rr}	I_F=20A, di/dt=100A/us		1.6		
Reverse Recovery Time	t_{rr}			11		ns
Turn-on Delay Time	$t_{D(on)}$	V_{GS}=10V, V_{DD}=15V,R_L=0.75Ω R_{GEN}=3Ω		11		
Turn-on Rise Time	t_r			80		
Turn-off Delay Time	$t_{D(off)}$			39		
Turn-off fall Time	t_f			92		

A. Pulse Test: Pulse Width≤300us,Duty cycle ≤2%.
B. The power dissipation P_D is based on $T_{J(MAX)}$=150℃, using junction-to-case thermal resistance, and is more useful in setting the upper dissipation limit for cases where additional heatsinking is used.
C. The value of $R_{\theta JA}$ is measured with the device mounted on 1in2 FR-4 board with 2oz. Copper, in a still air environment with T_A =25℃.
D. T_j=25℃, V_{DD}=25V, V_G=10V, L=1.0mH, I_{AS}=14A.

■ Typical Performance Characteristics

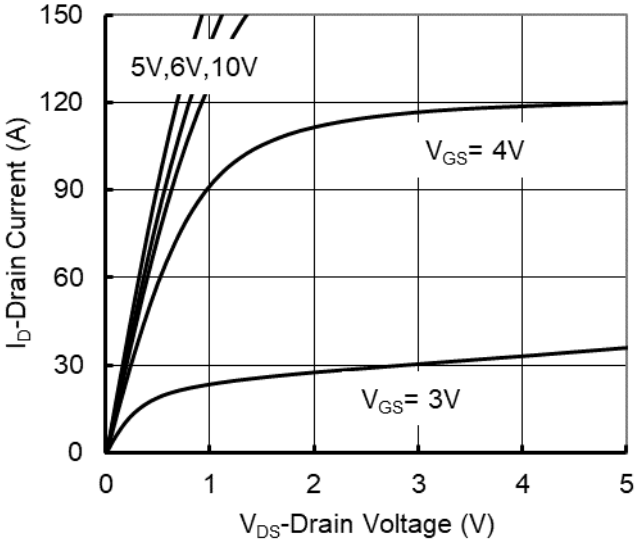


Figure 1. Output Characteristics

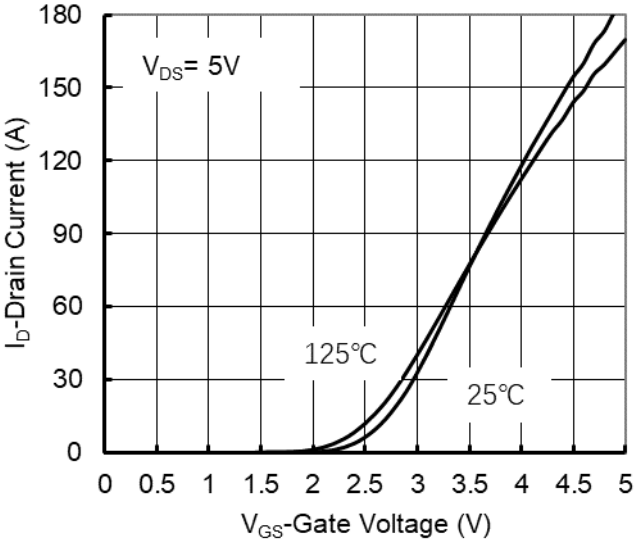


Figure 2. Transfer Characteristics

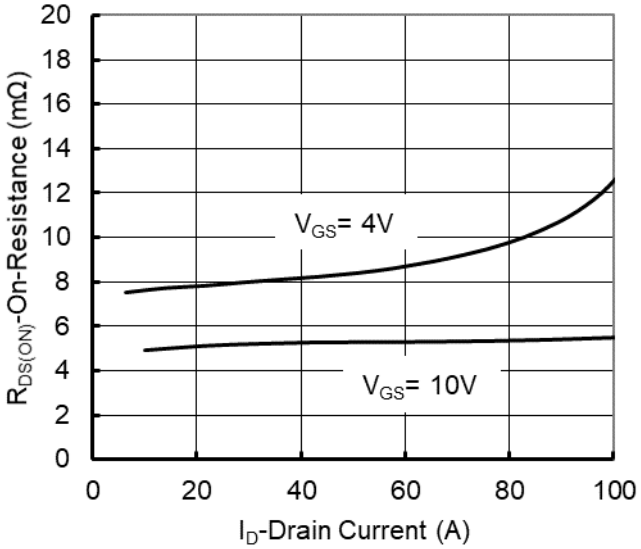


Figure 3. On-Resistance vs. Drain Current and Gate Voltage

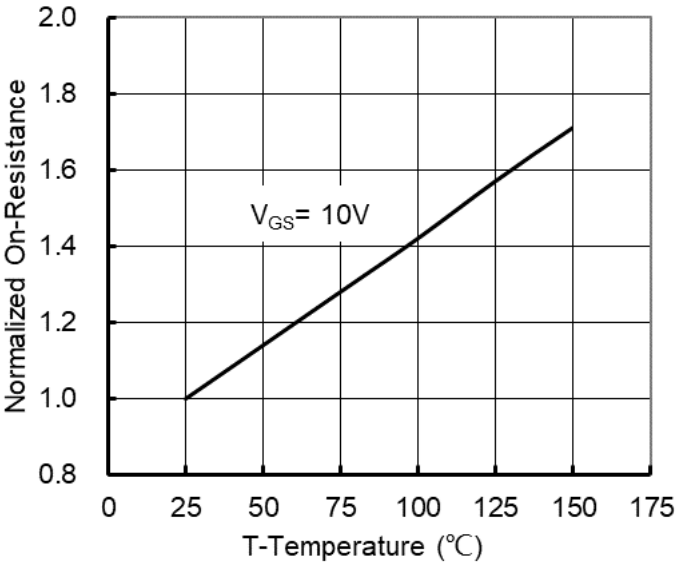


Figure 4. On-Resistance vs. Junction Temperature

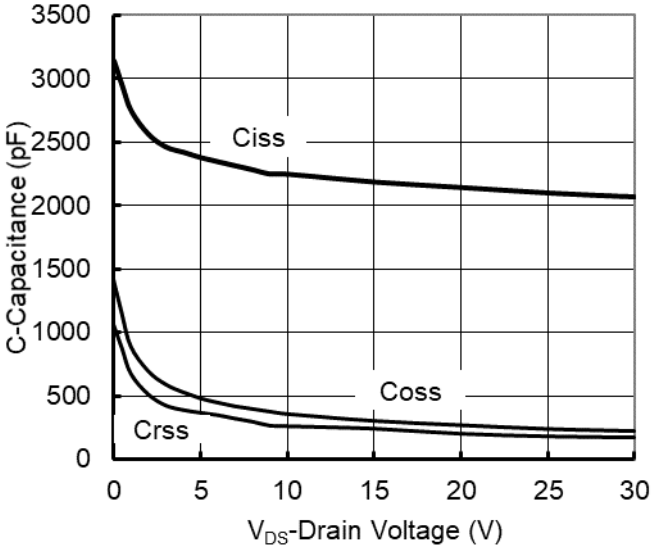


Figure 5. Capacitance Characteristics

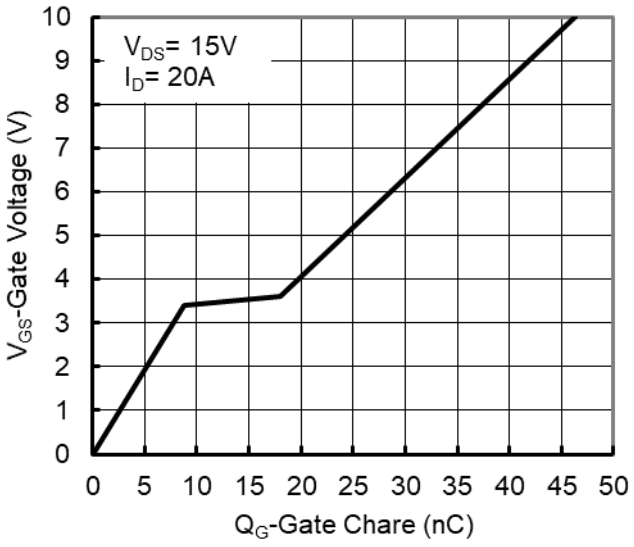


Figure 6. Gate Charge

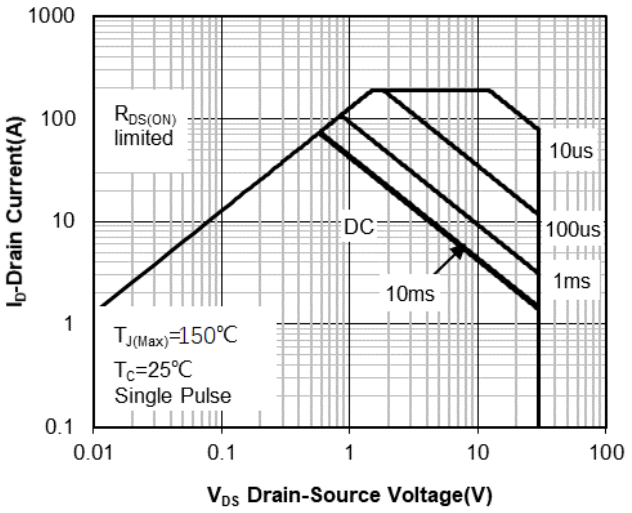


Figure 7. Safe Operation Area

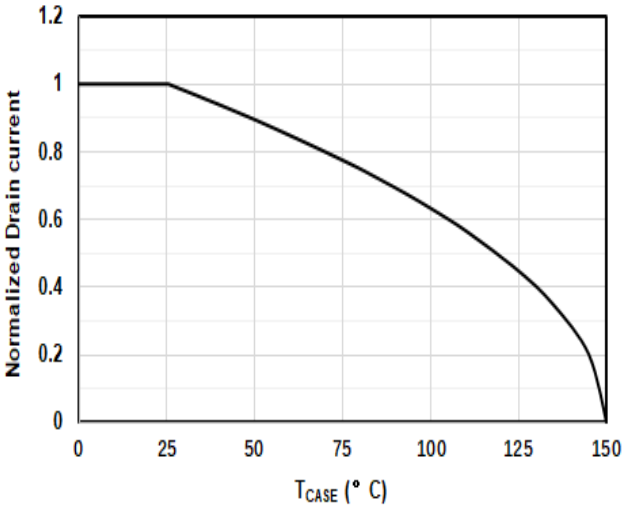


Figure 8. Maximum Continuous Drain Current vs Case Temperature

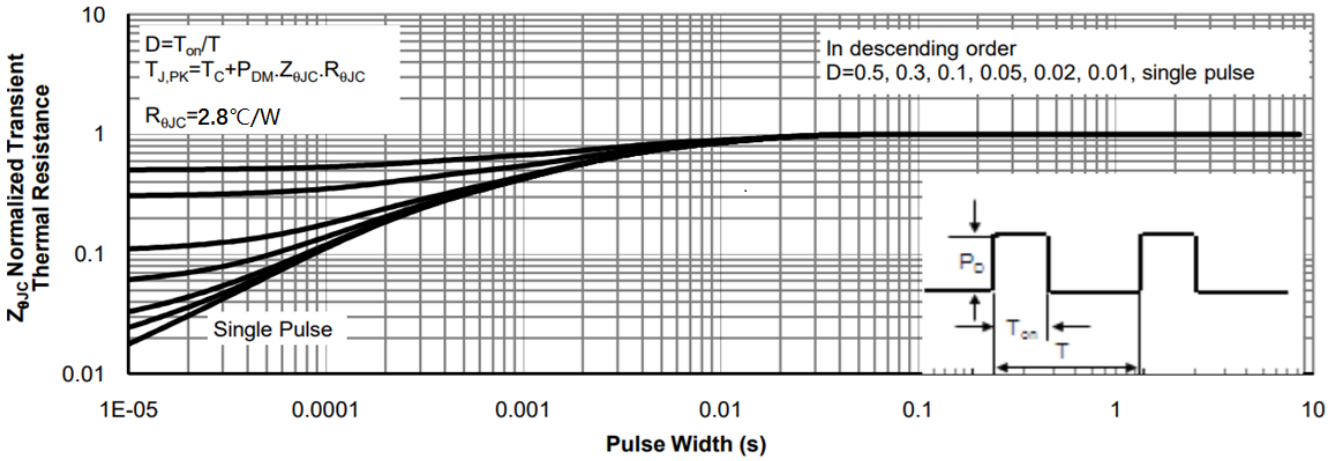
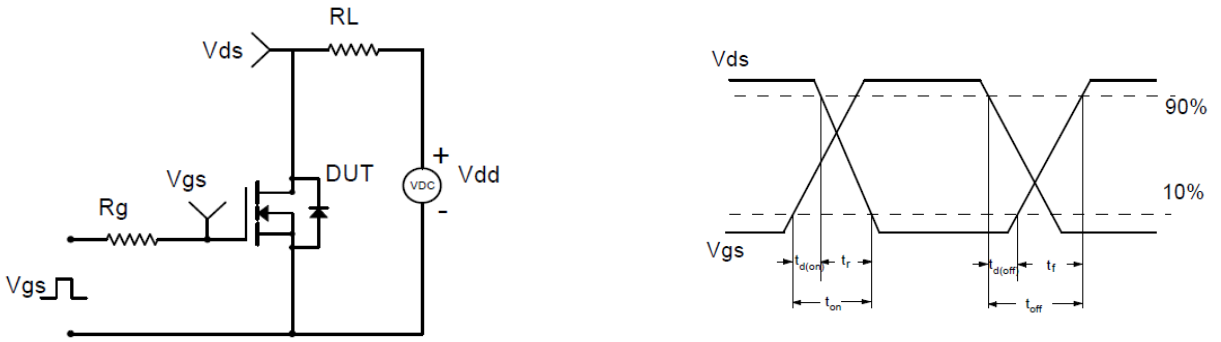
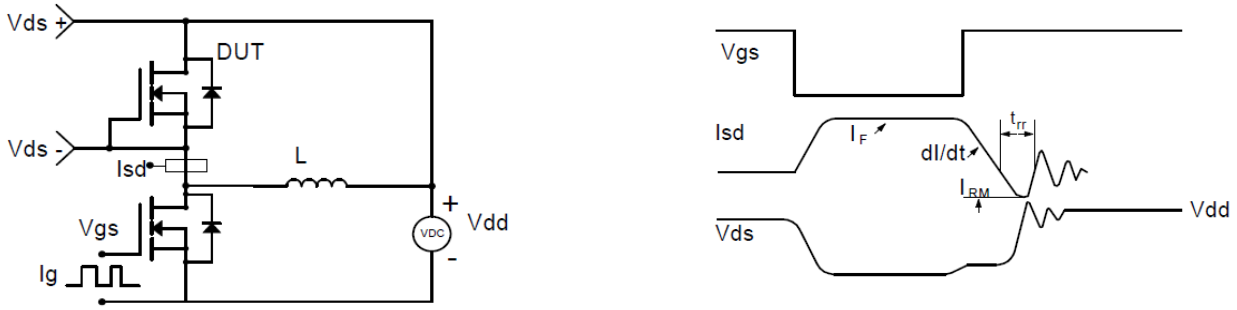


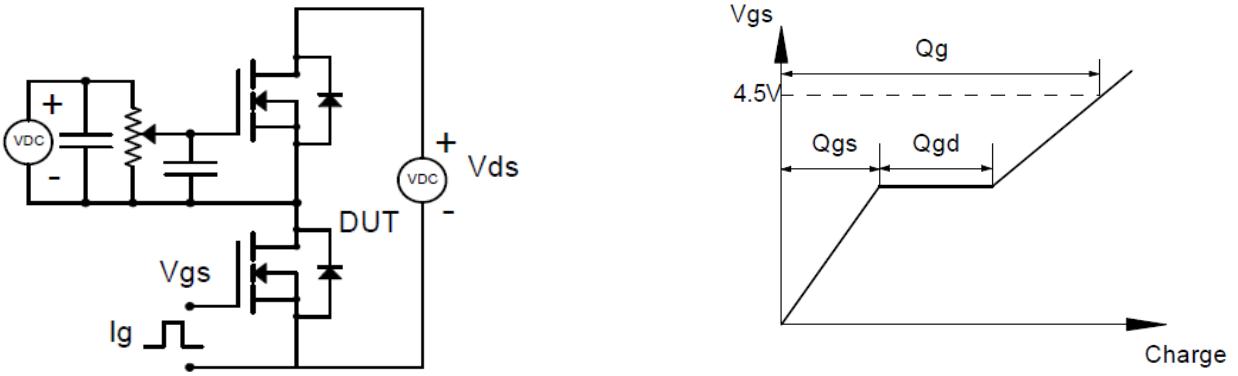
Figure 9. Normalized Maximum Transient Thermal Impedance



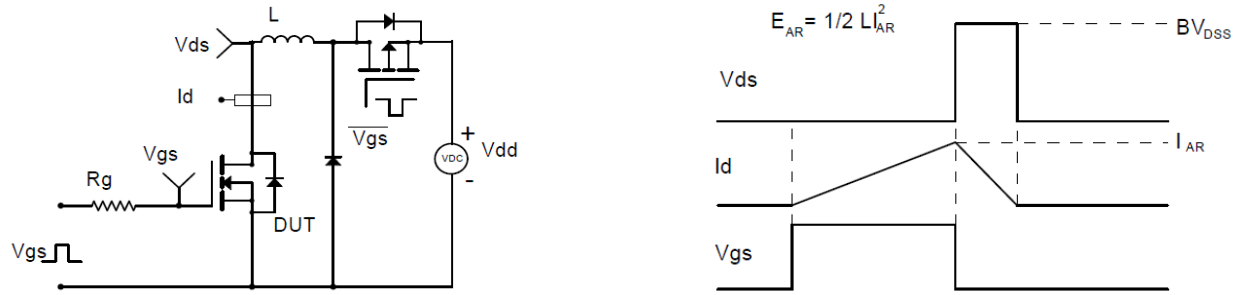
Resistive Switching Test Circuit & Waveforms



Diode Recovery Test Circuit & Waveforms

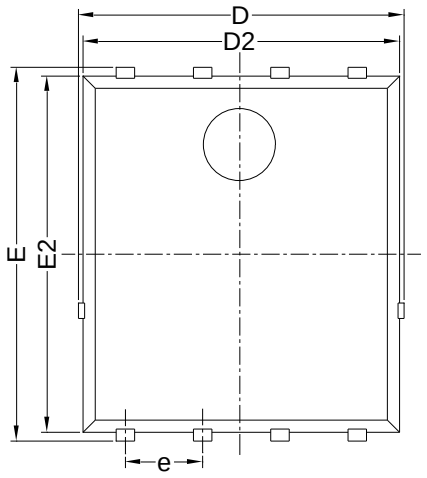


Gate Charge Test Circuit & Waveform

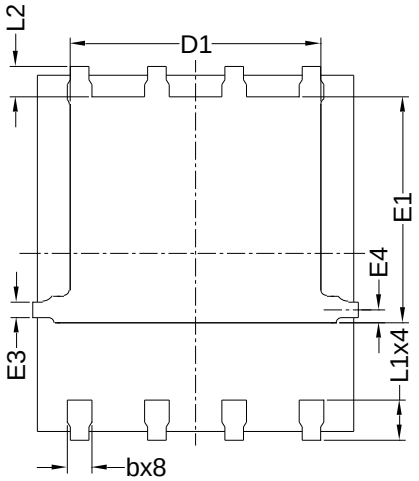


Unclamped Inductive Switching (UIS) Test Circuit & Waveforms

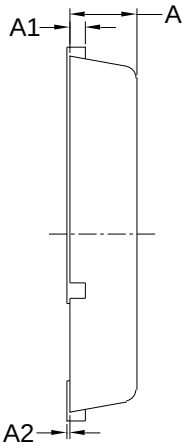
■ PDFN5060-8L-B-1.1MM Package Information



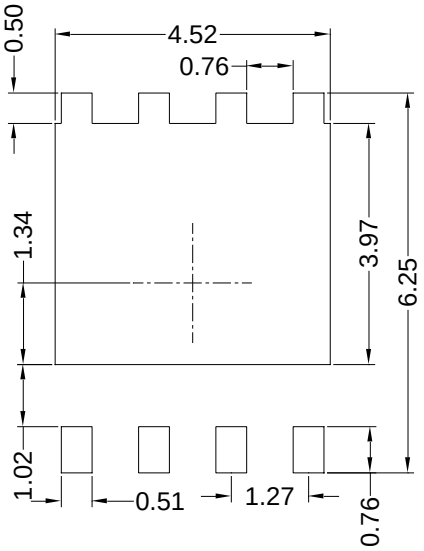
Top View
正面视图



Bottom View
背面视图



Side View
侧面视图



Suggested Solder Pad Layout
Top View

SYMBOL	MILLIMETER		
	MIN	NOM	MAX
D	5.15	5.35	5.55
E	5.95	6.15	6.35
A	1.00	1.10	1.20
A1		0.254 BSC	
A2			0.10
D1	3.92	4.12	4.32
E1	3.52	3.72	3.92
D2	5.00	5.20	5.40
E2	5.66	5.86	6.06
E3		0.254 REF	
E4		0.21 REF	
L1	0.56	0.66	0.76
L2		0.50 BSC	
b	0.31	0.41	0.51
e		1.27 BSC	

Note:
1.Controlling dimension:in millimeters.
2.General tolerance:±0.10mm.
3.The pad layout is for reference purposes only.

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